

| Form PTO-1449 | | | | Attorney Docket No. 062002-1752 | | Serial No. To Be Assigned | |
|---|------|---|--------------------|---|-------|-------------------------------------|----------------------------|
| INFORMATION DISCLOSURE CITATION | | | | Applicant Martin, et al. | | | |
| <i>(Use several sheets if necessary)</i> | | | | Filing Date Even Date Herewith | | Group 1763 | |
| U.S. PATENT DOCUMENTS | | | | | | | |
| Examiner Initials | Item | Document Number | Date | Name | Class | Subclass | Filing Date If Appropriate |
| <i>WJP</i> | 1A | 1,712,407 | 5/7/1929 | Skaupy | | | |
| <i>WJP</i> | 1B | 2,037,075 | 4/14/1936 | Haines | 250 | 27.5 | |
| <i>WJP</i> | 1C | 3,304,456 | 2/14/1967 | De Lany et al. | 313 | 182 | |
| <i>WJP</i> | 1D | 3,879,597 | 4/22/1975 | Bersin et al. | 219 | 121 | |
| <i>WJP</i> | 1E | 4,031,424 | 6/21/1977 | Penfold et al. | 313 | 146 | |
| <i>WJP</i> | 1F | 4,207,158 | 6/10/1980 | Freeman | 204 | 180 | |
| <i>WJP</i> | 1G | 4,259,145 | 3/31/1981 | Harper et al. | 156 | 643 | |
| <i>WJP</i> | 1H | 4,298,443 | 11/3/1981 | Maydan | 204 | 192 | |
| <i>WJP</i> | 1I | 4,309,267 | 1/5/1982 | Boyd et al. | 204 | 298 | |
| <i>WJP</i> | 1J | 4,450,787 | 5/29/1984 | Weakliem et al. | 118 | 723 | |
| <i>WJP</i> | 1K | 4,464,223 | 05/1999 | Gorin <i>08/1984</i> | 438 | 729 | |
| <i>WJP</i> | 1L | 4,496,881 | 1/29/1985 | Cheever | 315 | 357 | |
| FOREIGN PATENT DOCUMENTS | | | | | | | |
| | | Document Number | Date | Country | Class | Subclass | Translation |
| | | | | | | | Yes No |
| | 1M | | | | | | |
| | 1N | | | | | | |
| OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.) | | | | | | | |
| <i>WJP</i> | 1O | P. Breisacher et al. "Comparative Stabilities of Gaseous Alane, Gallane and Indane" Journal of the American Chemical Society pp. 4255-4258 87:19 Oct 5, 1965. | | | | | |
| <i>WJP</i> | 1P | S. Veprek et al. "The Preparation of Thin Layers of Ge and Si by Chemical Hydrogen Plasma Transport." Solid-State Electronics Pergamon Press 1968 vol. 11 pp. 683-684. | | | | | |
| <i>WJP</i> | 1Q | E. Wiberg et al "Hydrides of the Elements of Main Groups I-IV" New York 1971 Chapter 6 pp. 443-460. | | | | | |
| <i>WJP</i> | 1R | A.P. Webb "Reactivity of Solid Silicon with Hydrogen Under Conditions of a Low Pressure Plasma." Chemical Physics Letters vol 62 No 1 Mar 15, 1979 pp 173-177. | | | | | |
| <i>WJP</i> | 1W | S. Veprek et al. "Parameters Controlling the Deposition of Amorphous and Microcrystalline Silicon in Si/H Discharge Plasmas." Journal De Physique (Paris) 42 C4-251 (1981). | | | | | |
| * EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant. | | | | | | | |
| EXAMINER'S SIGNATURE: <i>Maureen J. Chan</i> | | | | DATE CONSIDERED: <i>6/4/2005</i> | | | |

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| Form PTO-1449 | | | | Attorney Docket No. 062002-1752 | | Serial No. To Be Assigned 10/784697 | |
| INFORMATION DISCLOSURE CITATION | | | | Applicant Martin, et al. | | Filing Date Even Date Herewith | |
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| Examiner Initials | Item | Document Number | Date | Name | Class | Subclass | Filing Date If Appropriate |
| msc | 4A | 5,631,978 | 5/20/1997 | Galand et al. | 382 | 240 | |
| msc | 4B | 5,660,744 | 8/26/1997 | Sekine et al. | 219 | 121.43 | |
| msc | 4C | 5,882,538 | 3/16/1999 | Martin et al. | 216 | 71 | |
| msc | 4D | 5,890,102 | 3/30/1999 | Kossentini et al. | 702 | 181 | |
| msc | 4E | 5,906,684 | 05/19/99 | Tamura et al. | 118 | 728 | |
| msc | 4F | 5,917,285 | 6/29/1999 | Gillis et al. | 313 | 632 | |
| msc | 4G | 5,983,828 | 11/1999 | Savas, Stephen E. | 118 | 723 | |
| msc | 4H | 6,033,587 | 3/7/2000 | Martin et al. | 216 | 71 | |
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| msc | 4J | 6,258,287 | 7/10/2001 | Martin et al. | 216 | 71 | |
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| FOREIGN PATENT DOCUMENTS | | | | | | | |
|--------------------------|----|-----------------|------|---------|-------|----------|-------------|
| | | Document Number | Date | Country | Class | Subclass | Translation |
| | | | | | | | Yes No |
| | 4K | | | | | | |
| | 4L | | | | | | |

| OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.) | | |
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| msc | 4M | H.P. Gillis et al "Highly Anisotropic, Ultra-smooth Patterning of GaN/SiC by Low Energy Electron Enhanced Etching in DC Plasma" J. Electronic Mat 26, 301-305 (1997) pp 1-16. |
| | 4N | |
| | 4O | |

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